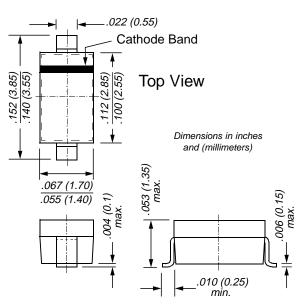
# GENERAL SEMICONDUCTOR<sup>®</sup>

# \*

#### SOD-123



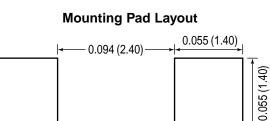
## **Mechanical Data**

Case: SOD-123 Plastic Package Weight: approx. 0.01g Marking Codes: BAT42W = L2 BAT43W = L3

#### Packaging Codes/Options:

D3/10K per 13" reel (8mm tape) D4/3K per 7" reel (8mm tape)

# BAT42W, BAT43W Schottky Diodes



#### **Features**

- For general purpose applications
- These diodes feature very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- These diodes are also available in the DO-35 case with the type designations BAT42 to BAT43 and in the MiniMELF case with the type designations LL42 to LL43.

## Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Parameters	Symbol	Value	Unit V	
Repetitive Peak Reverse Voltage	Vrrm	30		
Forward Continuous Current at T <sub>amb</sub> = 25°C	lF	200	mA	
Repetitve Peak Forward Current at tp < 1s, $\delta$ < 0.5, T <sub>amb</sub> = 25°C	IFRM	500	mA	
Surge Forward Current at $t_p < 10$ ms, $T_{amb} = 25^{\circ}C$	IFSM	4 <sup>(1)</sup>	А	
Power Dissipation <sup>(1)</sup> at T <sub>amb</sub> = 65°C	Ptot	200 <sup>(1)</sup>	mW	
Thermal Resistance Junction to Ambient Air	Røja	300 <sup>(1)</sup>	°C/W	
Junction Temperature	Tj	125	٥C	
Ambient Operating Temperature Range	Tamb	-55 to +125	°C	
Storage Temperature Range	Ts	-55 to +150	°C	

Note: (1) Valid provided that electrodes are kept at ambient temperature



# Electrical Characteristics (TJ = 25°C unless otherwise noted)

Parameter		Symbol	Test Condition	Min	Тур	Max	Unit
Reverse Breakdown Voltage		V(BR)R	I <sub>R</sub> = 100μA (pulsed)	30	_	—	V
Leakage Current <sup>(1)</sup>		IR	VR = 25V VR = 25V, Tj = 100°C			0.5 100	μΑ
Forward Voltage <sup>(1)</sup>	BAT42W BAT42W BAT43W BAT43W	VF	IF = 200mA IF = 10mA IF = 50mA IF = 2mA IF = 15mA	  0.26 		1.0 0.4 0.65 0.33 0.45	V
Capacitance		Ctot	VR = 1V, f = 1MHz	_	7		pF
Reverse Recovery Time		t <sub>rr</sub>	$I_F = 10mA$ to $I_R = 10mA$ to $I_R = 1mA$ , $R_L = 100\Omega$	_		5	ns
Detection Efficiency		$\eta_{v}$	$\label{eq:RL} \begin{split} R_L &= 15 K \Omega, \ C_L = 300 pF, \\ f &= 45 M Hz, \ V_RF = 2V \end{split}$	80	_	_	%

Note:

(1) Pulse Test  $t_p < 300 \mu s$ ,  $\delta < 2\%$